TPS65632

SLVSCY2-MARCH 2015

TPS65632 Triple-Output AMOLED Display Power Supply

1 Features

- 2.9-V to 4.5-V Input Voltage Range
- Boost Converter 1 (V_{POS})
 - 4.6-V Output Voltage
 - 0.5% Accuracy (25°C to 85°C)
 - Dedicated Output Sense Pin
 - 300-mA Output Current
- Inverting Buck-Boost Converter (V_{NEG})
 - –1.5-V to –5.4-V Programmable Output Voltage
 - -4-V Default Output Voltage
 - 300-mA Output Current
- Boost Converter 2 (AV_{DD})
 - 5.8-V or 7.7-V Output Voltage
 - 30-mA Output Current
- Excellent Line Transient Regulation
- Short-Circuit Protection
- Thermal Shutdown
- 3-mm × 3-mm, 16-Pin WQFN Package

4 Simplified Schematic

2 Applications

AMOLED Displays

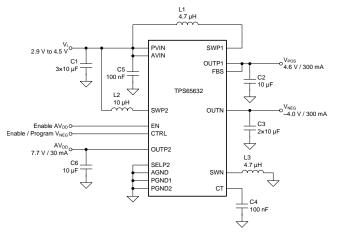
3 Description

The TPS65632 is designed to drive AMOLED displays (Active Matrix Organic Light Emitting Diode) requiring three supply rails, V_{POS} , V_{NEG} and AV_{DD} . The device integrates a boost converter for V_{POS} , an inverting buck-boost converter for V_{NEG} , and a boost converter for AV_{DD} , all of which are suitable for battery operated products. The digital control pin (CTRL) allows programming the negative output voltage in digital steps. The TPS65632 uses a novel technology enabling excellent line and load regulation.

Device Information⁽¹⁾

PART NUMBER	PACKAGE	BODY SIZE (NOM)
TPS65632	WQFN (16)	3.00 mm × 3.00 mm

(1) For all available packages, see the orderable addendum at the end of the datasheet.



Efficiency vs Output Current

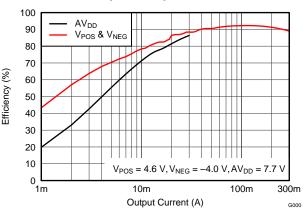


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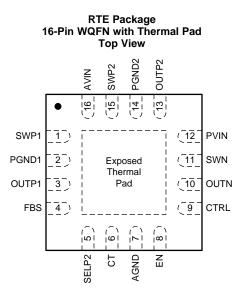
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5 Revision History

DATE	REVISION	NOTES
March 2015	*	Initial Release

6 Pin Configuration and Functions



Pin Functions

	PIN		DESCRIPTION		
NAME NO.		TYPE ⁽¹⁾			
AGND	7	GND	Analog ground.		
AVIN	16	PWR	Supply voltage for the device.		
СТ	6	I/O	A capacitor connected between this pin and ground sets the transition time for V_{NEG} when programmed to a new value.		
CTRL	9	I	Boost converter 1 (V_{POS}) inverting buck-boost converter (V_{NEG}) enable/program.		
EN	8	I	Boost converter 2 (AV _{DD}) enable.		
FBS	4	I	Boost converter 1 (V _{POS}) sense input.		
OUTN	10	0	Inverting buck-boost converter output (V _{NEG}).		
OUTP	3	0	Boost converter 1 output (V _{POS}).		
OUTP2	13	0	Boost converter 2 output (AV _{DD}).		
PGND1	2	GND	Boost converter 1 power ground.		
PGND2	14	GND	Boost converter 2 power ground.		
PVIN	12	PWR	Inverting buck-boost converter power stage supply voltage.		
SELP2	5	I	Boost converter 2 output voltage selection pin. AV_{DD} = 7.7 V when SELP2 = low and 5.8 V when SELP2 = high.		
SWN	11	I/O	Inverting buck-boost converter switch pin.		
SWP1	1	I	Boost converter 1 switch pin.		
SWP2	15	I	Boost converter 2 switch pin.		
Exposed ther	mal pad	_	Connect this pad to AGND, PGND1 and PGND2.		

(1) GND = Ground, PWR = Power, I = Input, O = Output, I/O = Input/Output

7 Specifications

7.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
	SWP1, OUTP1, FBS, PVIN, AVIN	-0.3	5	V
	SWP2	-0.3	12	V
	OUTP2	-0.3	8.5	V
Input supply voltage ⁽²⁾	OUTN	-6.0	0.3	V
	SWN	-6.5	4.8	V
	CTRL, EN, SELP2	-0.3	5.5	V
	СТ	-0.3	3.6	V
Operating virtual junction, T	J	-40	150	°C
Storage temperature, T _{stg}		-65	150	°C

(1) Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods my affect device reliability.

(2) With respect to GND pin.

7.2 ESD Ratings

			VALUE	UNIT
		Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins ⁽¹⁾	±2000	
V _(ESD)	Electrostatic discharge	Charged device model (CDM), per JEDEC specification JESD22-C101, all $\ensuremath{\text{pins}}^{(2)}$	±500	V

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

7.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
INPUT					
VI	Input supply voltage range	2.9	3.7	4.5	V
TJ	Operating junction temperature	-40	85	125	°C

7.4 Thermal Information

	THERMAL METRIC ⁽¹⁾	RTE [WQFN]	UNIT
		16 PINS	UNIT
$R_{\theta JA}$	Junction-to-ambient thermal resistance	42.9	
R _{0JC(top)}	Junction-to-case (top) thermal resistance	44	
$R_{ extsf{ heta}JB}$	Junction-to-board thermal resistance	14.2	8CAN
ΨJT	Junction-to-top characterization parameter	0.6	°C/W
Ψ _{JB}	Junction-to-board characterization parameter	14.1	
R _{0JC(bot)}	Junction-to-case (bottom) thermal resistance	3.3	

(1) For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953.

7.5 Electrical Characteristics

 V_I = 3.7 V, CTRL = 3.7 V, EN = 3.7 V, V_{POS} = 4.6 V, V_{NEG} = -4.0 V, AV_{DD} = 7.7 V, T_J = -40°C to 85°C, typical values are at T_J = 25°C (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
SUPPLY	CURRENT AND THERMAL PRO	TECTION				
VI	Input voltage range		2.9	3.7	4.5	V
I _{SD}	Shutdown current	CTRL = GND, EN = GND, sum of current flowing into AVIN and PVIN		0.25	5	μA
. ,		V _I falling	1.8		2.1	V
V _{UVLO}	Under-voltage lockout threshold	V _I rising	2.1		2.5	V
BOOST	CONVERTER 1 (V _{POS})	·				
	Positive output 1 voltage			4.6		V
V _{POS}	Positive output 1 voltage	$25^{\circ}C \le T_A \le 85^{\circ}C$, No load	-0.5%		0.5%	
	variation	$-30^{\circ}C \le T_A \le 85^{\circ}C$, No load	-0.8%		0.8%	
r _{DS(on)1A}	Switch on-resistance	1 200 mA		200		mΩ
r _{DS(on)1B}	Rectifier on-resistance	I _(SWP1) = 200 mA		350		mΩ
f _{SW1}	Switching frequency	I _{POS} = 200mA		1.7		MHz
I _{SW1}	Switch current limit	Inductor valley current	0.8	1	1.4	А
V _{SCP1}	Short-circuit threshold in operation	V _{POS} falling	3.95	4.10	4.28	V
t _{SCP1}	Short-circuit detection time in operation			3		ms
V_	Output voltage sense threshold	$V_{(OUTP1)} - V_{(FBS)}$ increasing	200	300	550	mV
VT	Ouput voltage sense timeshold	$V_{(OUTP1)} - V_{(FBS)}$ decreasing	100	200	450	mV
R _(FBS)	FBS pin pull-down resistance		2	4	6	MΩ
R _{DCHG1}	Discharge resistance	CTRL = GND, I _(SWP1) = 1mA	10	30	70	Ω
	Line regulation	I _{POS} = 200mA		0.01		%/V
	Load regulation	$1 \text{ mA} \le I_{POS} \le 300 \text{ mA}$		0.007		%/A
INVERTI	NG BUCK-BOOST CONVERTER	(V _{NEG})				
	Output voltage default			-4.0		V
V _{NEG}	Output voltage range		-1.4		-5.4	v
• NEG	Output voltage accuracy	$25^{\circ}C \le T_A \le 85^{\circ}C$, no load	-50		50	mV
		$-30^{\circ}C \le T_A \le 85^{\circ}C$, no load	-60		60	
r _{DS(on)2A}	SWN MOSFET on-resistance			200		mΩ
r _{DS(on)2B}	SWN MOSFET rectifier on- resistance	I _(SWN) = 200 mA		300		mΩ
f _{SW2}	SWN Switching frequency	I _{NEG} = 10 mA		1.7		MHz
I _{SW2}	SWN switch current limit	V _I = 2.9 V	1.5	2.2	3	Α
V _{SCP2}	Short circuit threshold in operation	Voltage increase from nominal V _{NEG}	300	500	700	mV
	Short circuit threshold in start up		180	200	230	mV
+	Short circuit detection time in start up			10		ms
t _{SCP2}	Short circuit detection time in operation			3		ms
R _{DCHG2}	Discharge resistance	CTRL = GND, I _(SWN) = 1 mA	130	150	170	Ω
	Line regulation	I _{NEG} = 200 mA		0.004		%/V
		INEG - 200 HINT		0.001		

Electrical Characteristics (continued)

 V_{I} = 3.7 V, CTRL = 3.7 V, EN = 3.7 V, V_{POS} = 4.6 V, V_{NEG} = -4.0 V, AV_{DD} = 7.7 V, T_{J} = -40°C to 85°C, typical values are at T_{J} = 25°C (unless otherwise noted)

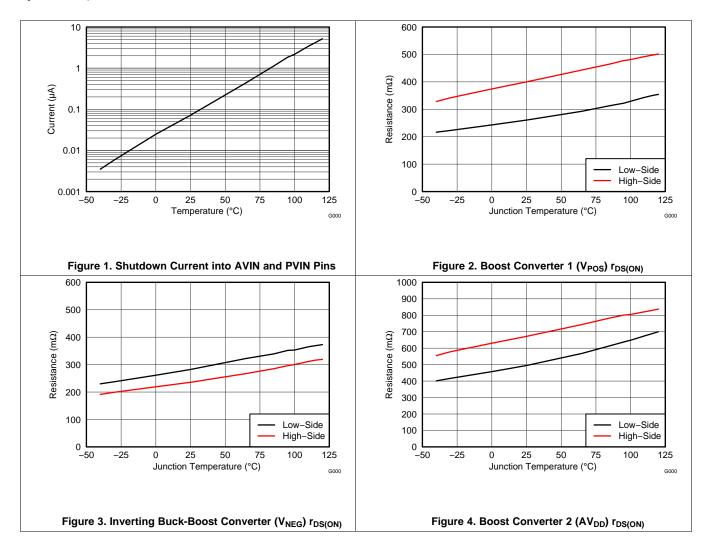
	PARAMETER	TEST CONDITIONS	MIN	ТҮР	MAX	UNIT
		SELP2 = Low		7.7		V
A.\/	Output voltage	SELP2 = High		5.8		V
AV _{DD}		$25^{\circ}C \le T_{A} \le 85^{\circ}C$, no load	-1%		1%	
	Output voltage accuracy	$-30^{\circ}C \le T_A \le 85^{\circ}C$, no load	-1.3%		1.3%	
r _{DS(on)3A}	SWP2 switch on-resistance	$-200 m^{4}$		400		mΩ
r _{DS(on)3B}	SWP2 rectifier on-resistance	I _(SWP2) = 200 mA		650		11122
f _{SW3}	Switching frequency	$I_{AVDD} = 0 \text{ mA}$		1.7		MHz
I _{LIM3}	Switch current limit	Inductor valley current	0.25	0.35	0.45	А
R _{DCHG3}	Discharge resistance	EN = GND, I _(SWP2) = 1 mA	10	30	70	Ω
	Line regulation	I _{AVDD} = 30 mA		0.02		%/V
	Load regulation			0.18		%/mA
CTRL IN	ITERFACE (CTRL, EN, SELP2)					
VIH	Logic input high level voltage		1.2			V
V _{IL}	Logic input low level voltage				0.4	V
R	Pull-down resistance		150	400	860	kΩ
OTHER						
R _{CT}	CT pin resistance		150	300	500	kΩ
t _{INIT}	Initialization time			300	400	μs
t _{STORE}	Data storage/accept time period		30		80	μs
t _{SDN}	Shutdown time period		30		80	μs
T _{SD}	Thermal shutdown temperature	Temperature rising		145		°C

7.6 Timing Requirements

		MIN	NOM	MAX	UNIT
CTRL INT	TERFACE				
t _{LOW}	Low-level pulse duration	2	10	25	μs
t _{HIGH}	High-level pulse duration	2	10	25	μs
t _{OFF}	Shutdown pulse duration (CTRL = low)	200			μs

7.7 Typical Characteristics

 $T_J = 25^{\circ}C$, $V_I = 3.7$ V, unless otherwise stated.

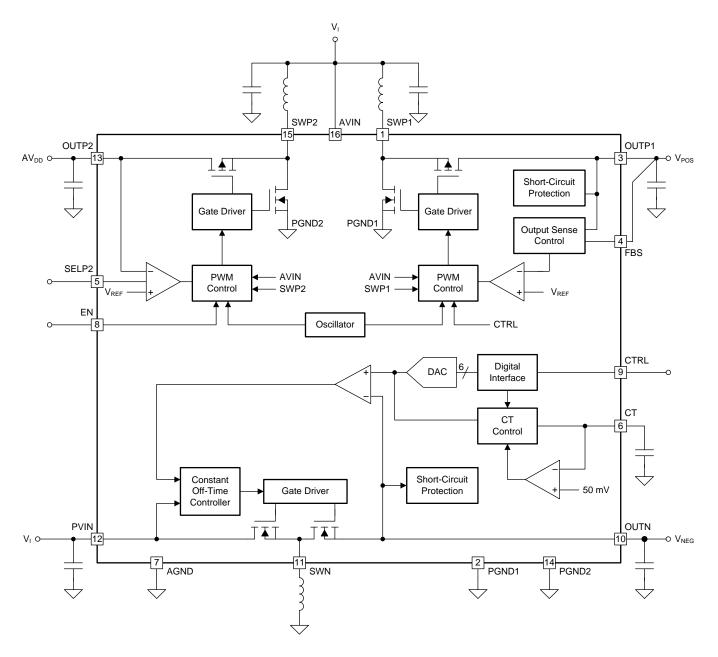


8 Detailed Description

8.1 Overview

The TPS65632 consists of two boost converters and an inverting buck-boost converter. The V_{POS} output is fixed at 4.6 V and V_{NEG} is programmable via a digital interface in the range of –1.4 V to –5.4 V; the default is –4 V. AV_{DD} can be selected between 7.7 V and 5.8 V, using the SELP2 pin. The transition time of V_{NEG} output is adjustable by the CT pin capacitor.

8.2 Functional Block Diagram



8.3 Feature Description

8.3.1 Boost Converter 1 (V_{POS})

Boost converter 1 uses a fixed-frequency current-mode topology. Its output voltage (V_{POS}) is programmed at the factory to 4.6 V and cannot be changed by the user.

For highest output voltage accuracy, connect the output sense pin (FBS) directly to the positive terminal of the main output capacitor. If not used, the FBS pin can be left floating or connected to ground, in which case the boost converter senses the output voltage via the OUTP1 pin.

8.3.1.1 V_(POS) Boost Output Sense (FBS Pin)

 $V_{(POS)}$ boost has a dedicated output sense pin (FBS). If FBS is floating or connected to ground, $V_{(POS)}$ boost senses the output through OUTP1 pin.

8.3.2 Inverting Buck-Boost Converter (V_{NEG})

The inverting buck-boost converter uses a constant-off-time current-mode topology. The converter's default output voltage (V_{NEG}) is -4.0 V, but it can be programmed from -1.4 V to -5.4 V (see Programming V_{NEG}).

8.3.2.1 Programming V_{NEG}

The digital interface allows programming of V_{NEG} in discrete steps. If the output voltage setting function is not required then the CTRL pin can also be used as a standard enable pin. The digital output voltage programming of V_{NEG} is implemented using a simple digital interface with the timing shown in Figure 5.

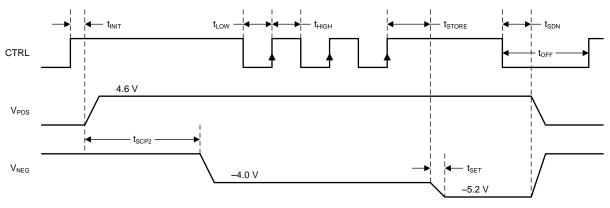


Figure 5. Digital Interface Using CTRL

When CTRL is pulled high the device starts up with its default voltage of -4 V. The device includes a 6-bit DAC that generates the output voltages shown in Table 1. The interface counts the rising edges applied to the CTRL pin once the device is enabled. According to Table 1, V_{NEG} is programmed to -5.2 V since 3 rising edges are detected.

Feature Description (continued)

Bit / Rising Edges	V _{NEG}	DAC Value	Bit / Rising Edges	V _{NEG}	DAC Value						
0 / no pulse	-4.0 V	000000	21	–3.4 V	010101						
1	–5.4 V	000001	22	–3.3 V	010110						
2	–5.3 V	000010	23	–3.2 V	010111						
3	–5.2 V	000011	24	–3.1 V	011000						
4	–5.1 V	000100	25	–3.0 V	011001						
5	–5.0 V	000101	26	–2.9 V	011010						
6	-4.9 V	000110	27	–2.8 V	011011						
7	-4.8 V	000111	28	–2.7 V	011100						
8	-4.7 V	001000	29	–2.6 V	011101						
9	-4.6 V	001001	30	–2.5 V	011110						
10	-4.5 V	001010	31	–2.4 V	011111						
11	-4.4 V	001011	32	–2.3 V	100000						
12	-4.3 V	001100	33	–2.2 V	100001						
13	-4.2 V	001101	34	–2.1 V	100010						
14	-4.1 V	001110	35	–2.0 V	100011						
15	-4.0 V	001111	36	–1.9 V	100100						
16	–3.9 V	010000	37	–1.8 V	100101						
17	–3.8 V	010001	38	-1.7 V	100110						
18	–3.7 V	010010	39	–1.6 V	100111						
19	–3.6 V	010011	40	–1.5 V	101000						
20	–3.5 V	010100	41	-1.4 V	101001						

Table 1.

8.3.2.2 Controlling V_{NEG} Transition Time

The transition time (t_{SET}) is the time required to move V_{NEG} from one voltage level to the next. Users can control the transition time with a capacitor connected between the CT pin and ground. When the CT pin is left open or connected to ground the transition time is as short as possible. When a capacitor is connected to the CT pin the transition time is determined by the time constant (τ) of the external capacitor ($C_{(CT)}$) and the internal resistance of the CT pin (R_{CT}). The output voltage reaches 70% of its programmed value after 1 τ .

An example is given when using 100 nF for $C_{(CT)}$.

 $T = 300 \text{ k}\Omega \times 100 \text{ nF} = 30 \text{ ms}$

(1)

The output voltage is at 70% of its final value after 1^T (i.e. 30 ms in this case) and at its final value after approximately 3^T (90 ms in this case).

8.3.3 Boost Converter 2 (AV_{DD})

Boost converter 2 uses a fixed-frequency current-mode topology. The TPS65632 device supports fixed output voltages of 5.8 V and 7.7 V, selected by the SELP2 pin. $AV_{DD} = 7.7$ V when SELP2 is low or left floating, and $AV_{DD} = 5.8$ V when SELP2 is high.

8.3.4 Soft Start and Start-Up Sequence

The devices feature a soft-start function to limit inrush current. Boost converter 2 (AV_{DD}) is enabled when EN goes high. When CTRL goes high, boost converter 1 starts with a reduced switch current limit and 10 ms later the inverting buck-boost converter (V_{NEG}) starts with its default value of -4 V. The typical start-up sequence is shown in Figure 6. The two boost converters operate independently and boost converter 1 (V_{POS}) does not require boost converter 2 (AV_{DD}) to be in regulation in order for it to start.

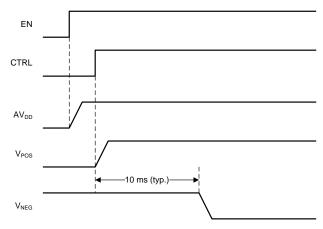


Figure 6. Start-Up Sequence

8.3.5 Enable (CTRL)

The CTRL pin serves two functions: one is to enable and disable the device, and the other is to program the output voltage (V_{NEG}) of the inverting buck-boost converter (see *Programming* V_{NEG}). If the V_{NEG} programming function is not required the CTRL pin can be used as a standard enable pin for the device, which will start up with its default value of -4.0 V on V_{NEG} . The device is enabled when CTRL is pulled high and disabled when CTRL is pulled low.

Note that to ensure proper start up CTRL must be pulled low for a minimum of 200 µs before being pulled high again.

8.3.6 Undervoltage Lockout

The device features an undervoltage lockout function that disables it when the input supply voltage is too low for proper operation.

8.3.7 Short-Circuit Protection

8.3.7.1 Short Circuits During Operation

The device is protected against short circuits of V_{POS} and V_{NEG} to ground and short circuit of these two outputs to each other. During normal operation an error condition is detected if V_{POS} falls below 4.1 V for longer than 3 ms or V_{NEG} is pulled above the programmed nominal output by 500 mV for longer than 3 ms. In either case the device goes into shutdown and the outputs are disconnected from the input. This state is latched, and to resume normal operation, V_I has to cycle below the undervoltage lockout threshold, or CTRL has to toggle LOW and then HIGH.

8.3.7.2 Short Circuits During Start Up

During start up an error condition is detected in the following cases:

- V_{POS} is not in regulation 10 ms after CTRL goes HIGH
- V_{NEG} is higher than threshold level 10 ms after CTRL goes HIGH
- V_{NEG} is not in regulation 20 ms after CTRL goes HIGH

If any of the above conditions is met the device goes into shutdown and the outputs are disconnected from the input. This state is latched, and to resume normal operation V_1 has to cycle below the undervoltage threshold, or CTRL has to toggle LOW and HIGH.

8.3.8 Output Discharge During Shut Down

The device discharges outputs during shutdown. Figure 7 shows the discharge control.

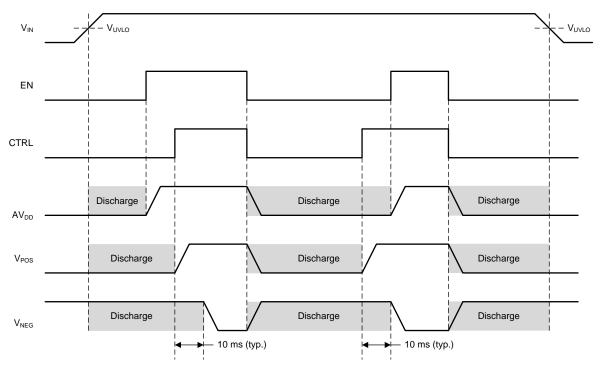


Figure 7. Outputs Discharge During Shut Down

8.3.9 Thermal Shutdown

The TPS65632 device enters thermal shutdown if its junction temperature exceeds $145^{\circ}C$ (typical). During thermal shutdown none of the device's functions are available. To resume normal operation V_I has to cycle below the undervoltage threshold, or CTRL has to toggle LOW and then HIGH.

8.4 Device Functional Modes

8.4.1 Operation with $V_1 < 2.9 V$

The recommended minimum input supply voltage for full-performance is 2.9 V. The device continues to operate with input supply voltages below 2.9 V, however, full performance is not guaranteed. The TPS65632 device does not operate with input supply voltages below the UVLO threshold.

8.4.2 Operation with $V_I \approx V_{POS}$ (Diode Mode)

The TPS65632 device features a "diode" mode that enables it to regulate its V_{POS} output even when the input supply voltage is close to V_{POS} (that is, too high for normal boost operation). When operating in diode mode the V_{POS} boost converter's high-side switch is disabled and its body diode used as the rectifier. Note that a minimum load of \approx 2 mA is required to proper output regulation in diode mode.

8.4.3 Operation with CTRL

When a low-level signal is applied to the CTRL pin the device is disabled and switching is inhibited. When the input supply voltage is above the UVLO threshold and a high-level signal is applied to the CTRL pin the device is enabled and its start-up sequence begins.

9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The TPS65632 device is intended to supply the main analog supplies required by AMOLED displays. V_{POS} is fixed at 4.6 V, but V_{NEG} can be programmed using the CTRL pin to voltages in the range –1.4 V to –5.4 V. The SELP2 pin can be used to set AV_{DD} to either 5.8 V or 7.7 V. The device is highly integrated and requires few external components.

9.2 Typical Application

Figure 8 shows a typical application circuit suitable for supplying AMOLED displays in smartphone applications. The circuit is designed to operate from a single-cell Li-Ion battery and generates a positive output voltage V_{POS} of 4.6 V, a negative output voltage V_{NEG} of -4.0 V, and a positive output voltage AV_{DD} of 5.8 V or 7.7 V. The V_{POS} and V_{NEG} outputs are each capable of supplying up to 300 mA of current, and the AV_{DD} output of up to 30 mA.

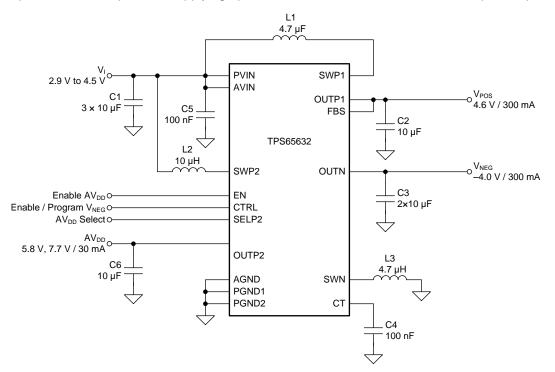


Figure 8. Typical Application Circuit

Typical Application (continued)

9.2.1 Design Requirements

For this design example, use the parameters shown in Table 2

Table	2. Desigr	Parameters
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PARAMETER	VALUE
Input voltage range	2.9 V to 4.5 V
Output voltage	V _{POS} = 4.6 V V _{NEG} = -4.0 V AV _{DD} = 7.7 V
Current	l _(VPOS) = 300 mA l _(VNEG) = 300 mA l _(AVDD) = 30 mA
Switching Frequency	$\begin{array}{l} f_{(SWP1)} = 1.7 \text{ MHz} \\ f_{(SWN)} = 1.7 \text{ MHz} \\ f_{(SWP2)} = 1.7 \text{ MHz} \end{array}$

9.2.2 Detailed Design Procedure

In order to maximize performance, the TPS65632 device has been optimized for use with a relatively narrow range of component values, and customers are strongly recommended to use the application circuits shown in Figure 8 with the components listed in Table 3 and Table 4.

9.2.2.1 Inductor Selection

The V_{POS} and V_{NEG} converters have been optimized for use with 4.7-µH inductors and the AV_{DD} boost converter has been optimized for use with 10-µH inductors. For optimum performance it is recommended that these values be used in all applications. Customers using different inductors than the ones in Table 3 are strongly recommended to characterize circuit performance fully before finalizing their design. Customers should pay particular attention to the inductors' saturation current and ensure it is adequate for their application's worst-case conditions (which may also be during start-up).

Table 3. Inductor Selection

REFERENCE DESIGNATOR	VALUE	MANUFACTURER	PART NUMBER		
L1, L3	4.7 µH	Coilcraft	XFL4020-4R7ML		
L2	10 µH	Coilmaster	MMPP252012-100N		

9.2.2.2 Capacitor Selection

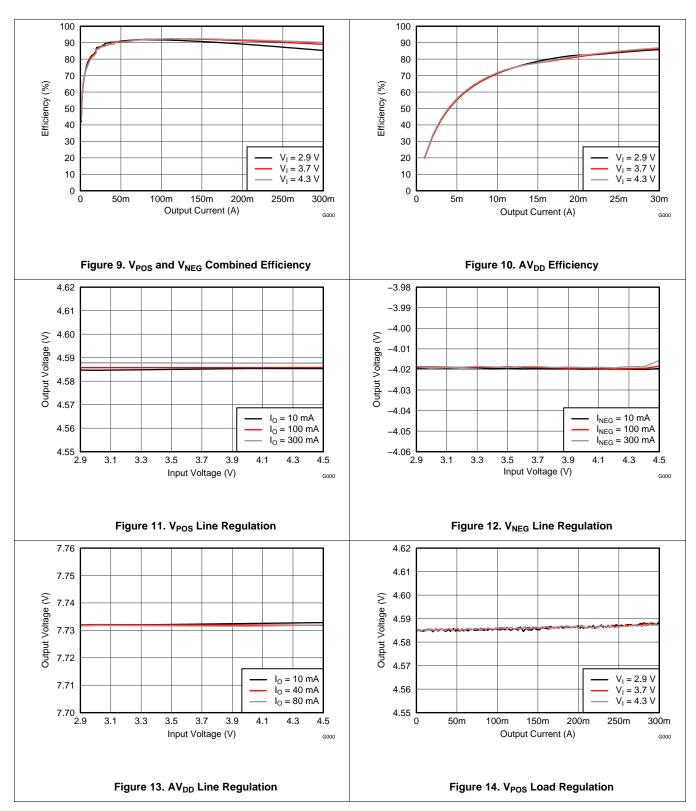
The recommended capacitor values are shown in Table 4. Applications using less than the recommended capacitance (e.g. to save PCB area) may exhibit increased voltage ripple. In general, the lower the output current, the lower the necessary capacitance. Customers should be aware that ceramic capacitors of the kind typically used with the TPS65632 device exhibit dc bias effects, which means their effective capacitance under normal operating conditions may be significantly lower than their nominal capacitance value. Customers must ensure that the *effective* capacitance is sufficient for their application's performance requirements.

REFERENCE DESIGNATOR	VALUE	MANUFACTURER	PART NUMBER
C1	3 × 10 μF	Murata	GRM21BR71A106KE51
C2, C6	10 µF	Murata	GRM21BR71A106KE51
C3	2 × 10 μF	Murata	GRM21BR71A106KE51
C4, C5	100 nF	Murata	GRM155B11A104KA01

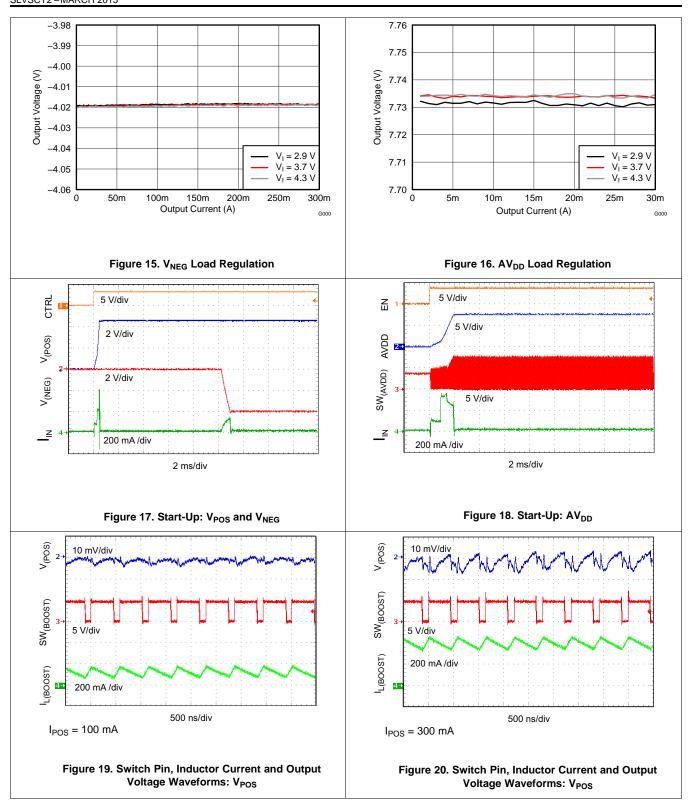
Table 4. Capacitor Selection

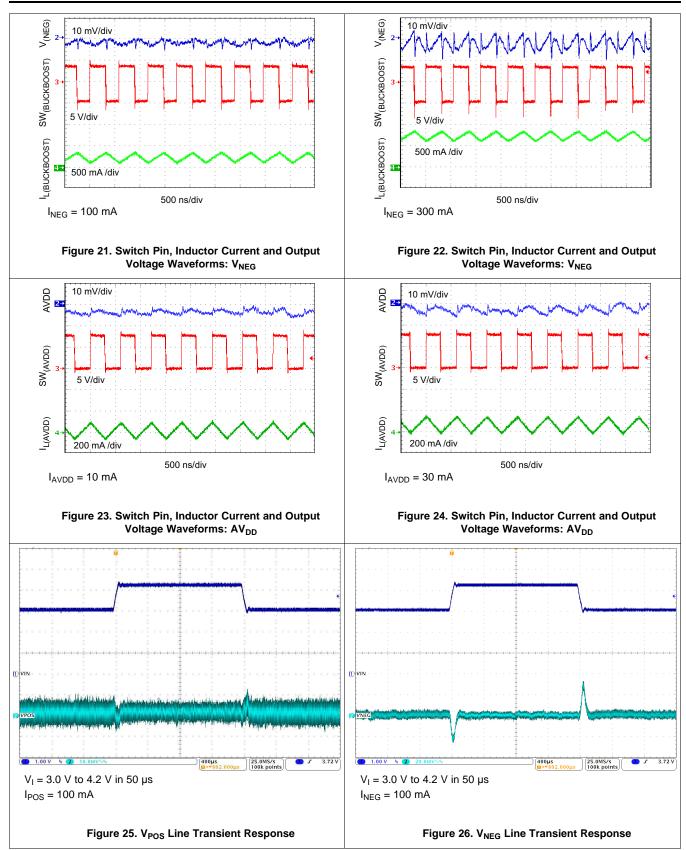
9.2.3 Application Curves

Unless otherwise stated: $T_A = 25^{\circ}$ C, $V_I = 3.7$ V, $V_{POS} = 4.6$ V, $V_{NEG} = -4.0$ V, $AV_{DD} = 7.7$ V; L1 = L3 = XFL4020-4R7ML, and L2 = MMPP252012-100N.

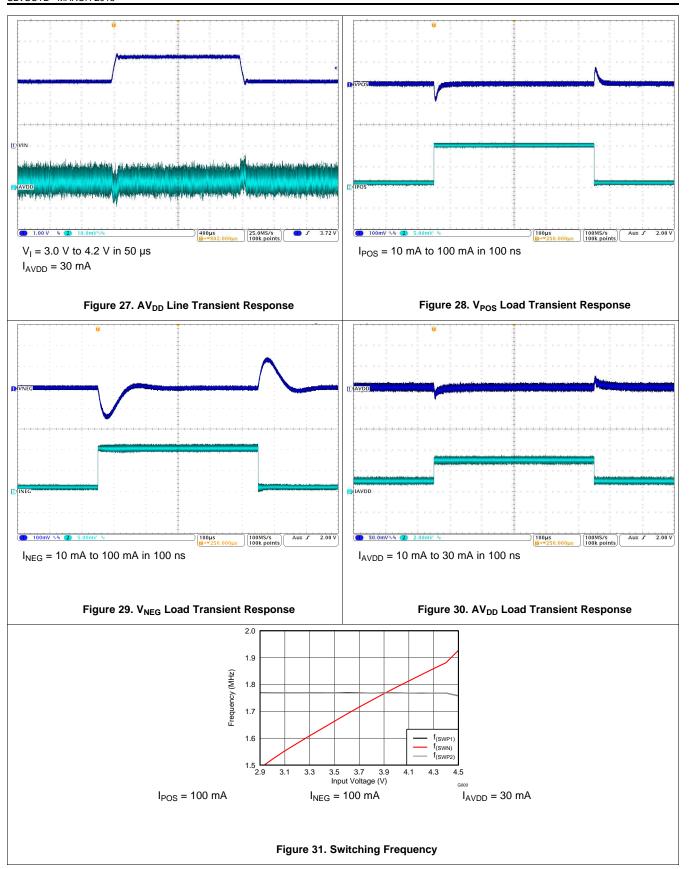


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10 Power Supply Recommendations

The TPS65632 device is designed to operate with input supply voltages in the range 2.9 V to 4.5 V. If the input supply voltage is located more than a few centimeters away from the device, additional bulk capacitance may be required. The three $10-\mu$ F capacitors shown in Figure 8 are suitable for typical applications.

11 Layout

11.1 Layout Guidelines

- Place the input capacitor on PVIN and the output capacitor on OUTN as close as possible to device. Use short and wide traces to connect the input capacitor on PVIN and the output capacitor on OUTN.
- Place the output capacitor on OUTP1 and OUTP2 as close as possible to device. Use short and wide traces to connect the output capacitor on OUTP1 and OUTP2.
- Connect the ground of CT capacitor with AGND, pin 7, directly.
- Connect input ground and output ground on the same board layer, not through via hole.
- Connect AGND, PGND1 and PGND2 with exposed thermal pad.

11.2 Layout Example

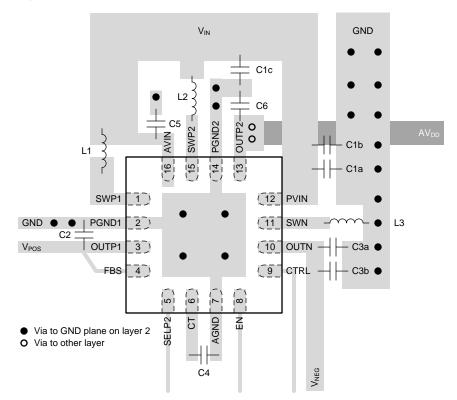


Figure 32. Recommended PCB Layout

12 Device and Documentation Support

12.1 Device Support

12.1.1 Third-Party Products Disclaimer

TI'S PUBLICATION OF INFORMATION REGARDING THIRD-PARTY PRODUCTS OR SERVICES DOES NOT CONSTITUTE AN ENDORSEMENT REGARDING THE SUITABILITY OF SUCH PRODUCTS OR SERVICES OR A WARRANTY, REPRESENTATION OR ENDORSEMENT OF SUCH PRODUCTS OR SERVICES, EITHER ALONE OR IN COMBINATION WITH ANY TI PRODUCT OR SERVICE.

12.2 Trademarks

12.3 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

12.4 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Ordering Information

The following pages include mechanical, packaging, and ordering information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGE OPTION ADDENDUM

29-Mar-2015

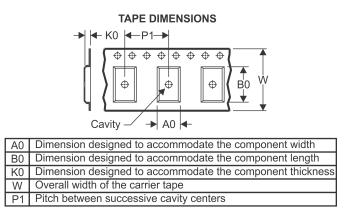
PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package	Pins	Package	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
TPS65632RTER	ACTIVE	WQFN	RTE	16	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	PC6I	Samples
TPS65632RTET	ACTIVE	WQFN	RTE	16	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	PC6I	Samples

28-Mar-2015

TAPE AND REEL INFORMATION





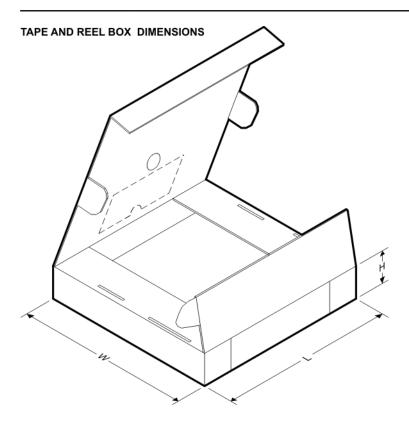
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS65632RTER	WQFN	RTE	16	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2
TPS65632RTET	WQFN	RTE	16	250	180.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2

PACKAGE MATERIALS INFORMATION

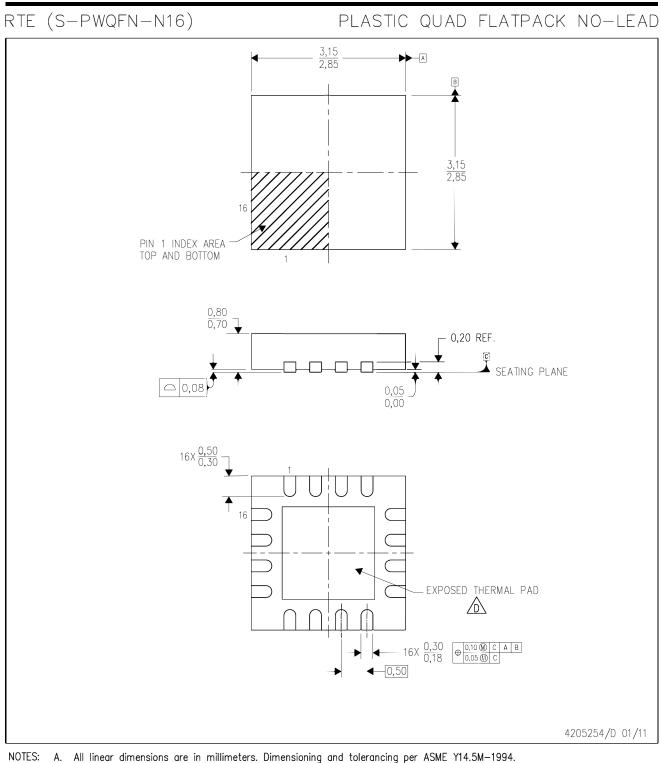
28-Mar-2015



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPS65632RTER	WQFN	RTE	16	3000	367.0	367.0	35.0
TPS65632RTET	WQFN	RTE	16	250	210.0	185.0	35.0

MECHANICAL DATA



A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.B. This drawing is subject to change without notice.

- C. Quad Flatpack, No-leads (QFN) package configuration.
- The package thermal pad must be soldered to the board for thermal and mechanical performance. See the Product Data Sheet for details regarding the exposed thermal pad dimensions. ∕∆
- E. Falls within JEDEC MO-220.

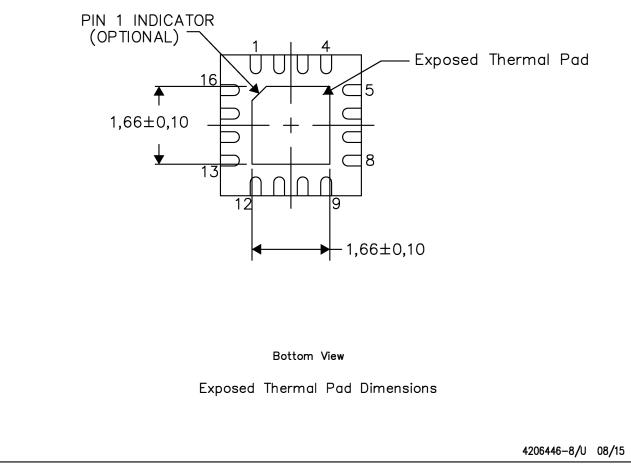
RTE (S-PWQFN-N16) PLASTIC QUAD FLATPACK NO-LEAD

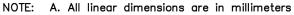
THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

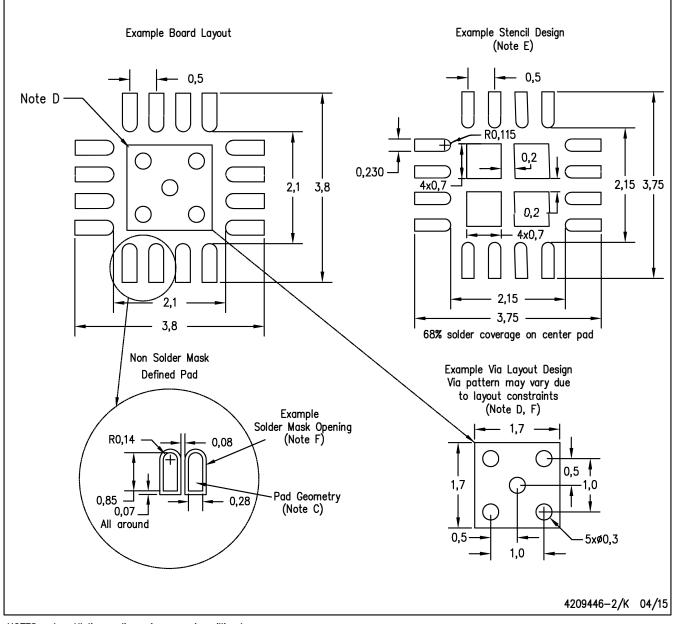
For information on the Quad Flatpack No-Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.





RTE (S-PWQFN-N16) PLASTIC QUAD FLATPACK NO-LEAD



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Application Note, Quad Flat—Pack Packages, Texas Instruments Literature No. SLUA271, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com http://www.ti.com.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
- F. Customers should contact their board fabrication site for minimum solder mask web tolerances between signal pads.